



Product Summary

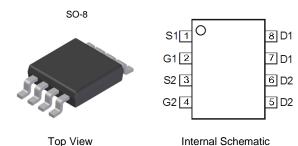
BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C	
30V	$20m\Omega$ @ $V_{GS} = 10V$	16A	
307	$32mΩ @ V_{GS} = 4.5V$	13A	

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters



Features

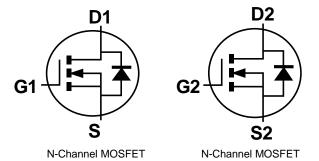
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



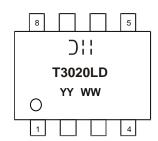
Ordering Information (Note 4)

ı	Part Number	Case	Packaging
	DMT3020LSD-13	SO-8	2500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 7) Steady State $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$			ΙD	16 13	А
Maximum Body Diode Forward Current (Note 7)	Is	8	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	50	Α
Pulsed Drain Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	50	Α
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	13	Α
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	8.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	117	°C/W
Total Power Dissipation (Note 6)		P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{ heta JA}$	81	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	20	C/VV	
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30.0	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	2.5	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance			_	20	mΩ	$V_{GS} = 10V, I_D = 9.0A$
Static Diani-Source On-Resistance	R _{DS(ON)}	_	_	32	11122	$V_{GS} = 4.5V, I_D = 7.0A$
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 2A$
DYNAMIC CHARACTERISTICS (Note 10)	<u> </u>					•
Input Capacitance	C _{iss}	l	393		рF	\\ A5\\\\\ 0\\
Output Capacitance	Coss	-	173	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	27	_	pF	7 = 1.0WH IZ
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	7.0	_	nC	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.6	_	nC	\
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{DD} = 15V, I_{D} = 9A$
Gate-Drain Charge	Q _{gd}	_	1.5	_	nC	
Turn-On Delay Time	t _{D(ON)}		1.8	_	ns	
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}		7.5	_	ns	$R_G = 6\Omega$, $I_D = 9A$
Turn-Off Fall Time	t _F		2.4	_	ns	7
Reverse Recovery Time	t _{RR}		10	_	ns	1 00 11/11 1000/
Reverse Recovery Charge	Q _{RR}		2.6	_	nC	$I_F = 9A$, $dI/dt = 100A/\mu s$

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

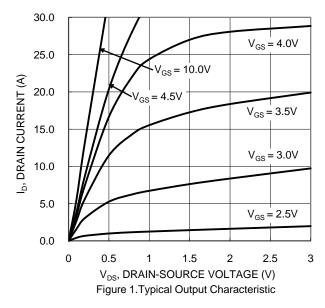
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} IAS and EAS ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





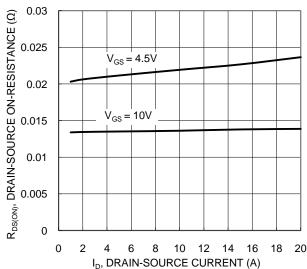


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

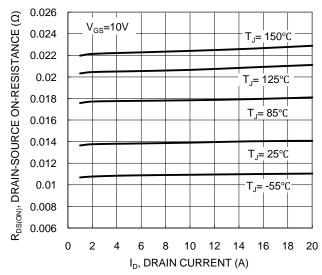
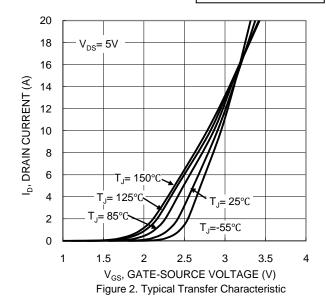
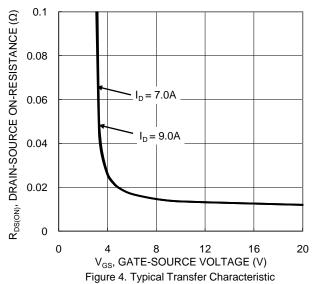


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





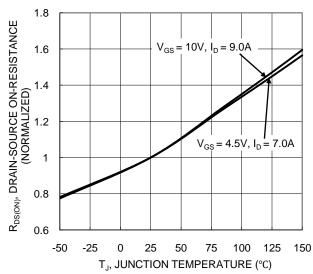


Figure 6. On-Resistance Variation with Temperature



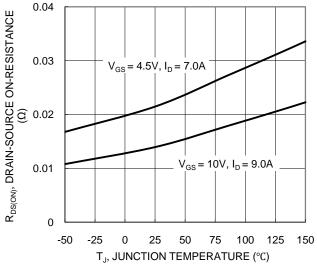


Figure 7. On-Resistance Variation with Temperature

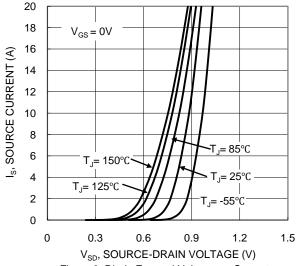
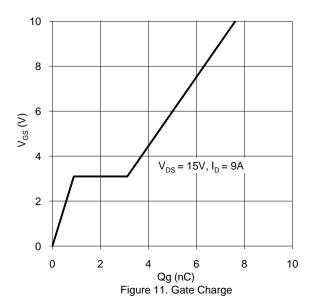
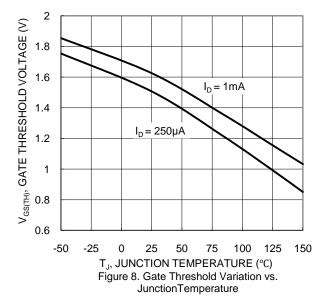
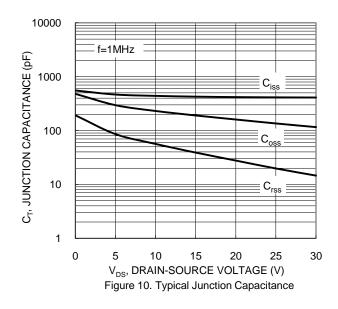
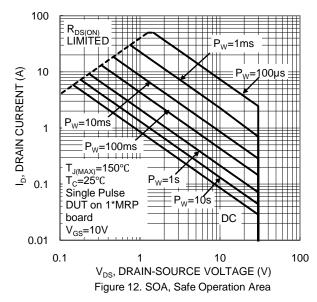


Figure 9. Diode Forward Voltage vs. Current











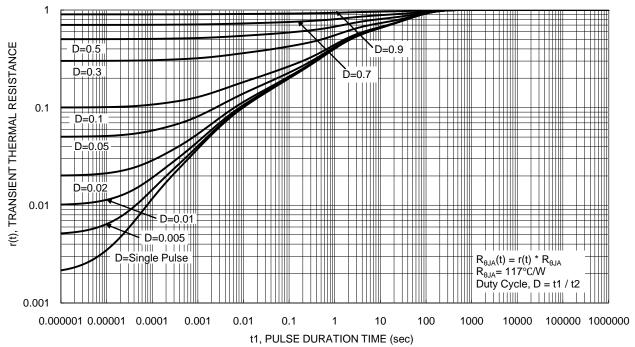
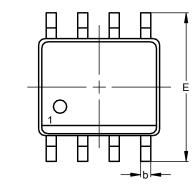


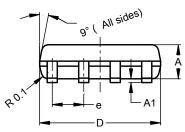
Figure 13. Transient Thermal Resistance

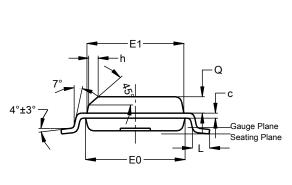


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.







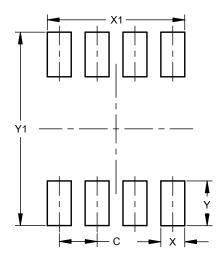
SO-8

SO-8						
Dim	Min	Max	Тур			
Α	1.40	1.50	1.45			
A1	0.10	0.20	0.15			
b	0.30	0.50	0.40			
С	0.15	0.25	0.20			
D	4.85	4.95	4.90			
Е	5.90	6.10	6.00			
E1	3.80	3.90	3.85			
E0	3.85	3.95	3.90			
е			1.27			
h	-		0.35			
L	0.62	0.82	0.72			
Q	0.60	0.70	0.65			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
Y1	6.50

March 2018



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